

Dual N-Channel Enhancement Mode MOSFET

Features

- 20V/6A, $R_{DS(ON)} = 16m\Omega$ (typ.) @ $V_{GS} = 4.5V$
 $R_{DS(ON)} = 19m\Omega$ (typ.) @ $V_{GS} = 2.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)

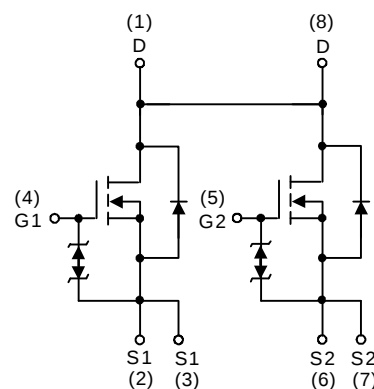
Pin Description



Top View of TSSOP – 8

Applications

- Power Management, Portable Equipment and Battery Powered Systems



N-Channel MOSFET

Ordering and Marking Information

APM9988C □□-□□□ Lead Free Code Handling Code Temp. Range Package Code	Package Code O : TSSOP-8 Operating Junction Temp. Range C : -55 to 150°C Handling Code TU : Tube TR : Tape & Reel Lead Free Code L : Lead Free Device Blank : Original Device
APM9988C O :	APM9988C XXXXX XXXXX - Date Code

Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS and compatible with both SnPb and lead-free soldering operations. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J STD-020C for MSL classification at lead-free peak reflow temperature.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
V _{DSS}	Drain-Source Voltage		20	V
V _{GSS}	Gate-Source Voltage		±8	
I _D *	Continuous Drain Current	V _{GS} =4.5V	6	A
I _{DM} *	300μs Pulsed Drain Current		20	
I _S *	Diode Continuous Forward Current		1.4	A
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
P _D *	Maximum Power Dissipation	T _A =25°C	1.25	W
		T _A =100°C	0.5	
R _{θJA} *	Thermal Resistance-Junction to Ambient		100	°C/W

Note:

*Surface Mounted on 1in² pad area, $t \leq 10\text{sec.}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	APM9988CO			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V			1	μA
		T _J =85°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	0.5	0.7	1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±8V, V _{DS} =0V			±10	μA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =4.5V, I _{DS} =6A		16	20	mΩ
		V _{GS} =2.5V, I _{DS} =5.2A		19	25	
V _{SD} ^a	Diode Forward Voltage	I _{SD} =0.5A, V _{GS} =0V		0.7	1.3	V
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =4.5V, I _{DS} =6A		16.5	21	nC
Q _{gs}	Gate-Source Charge			4.5		
Q _{gd}	Gate-Drain Charge			4.5		

Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

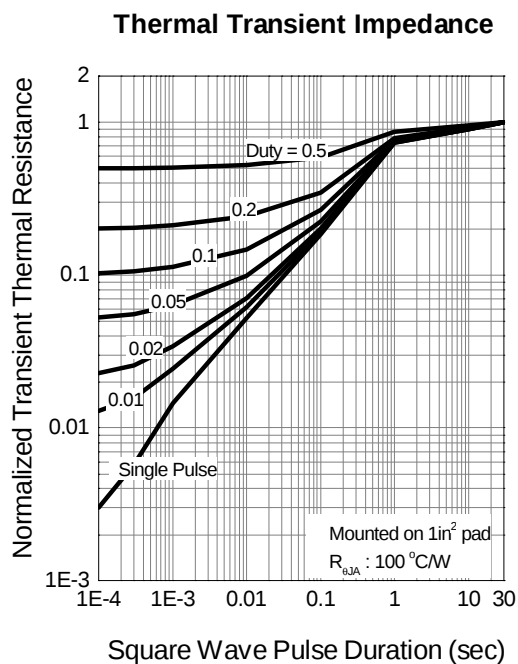
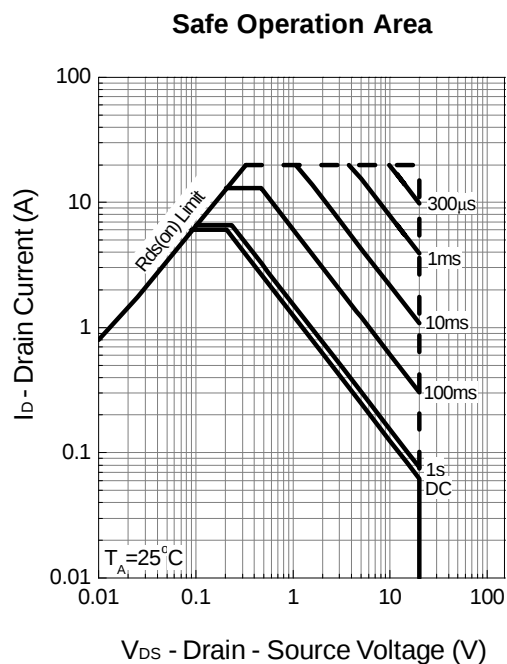
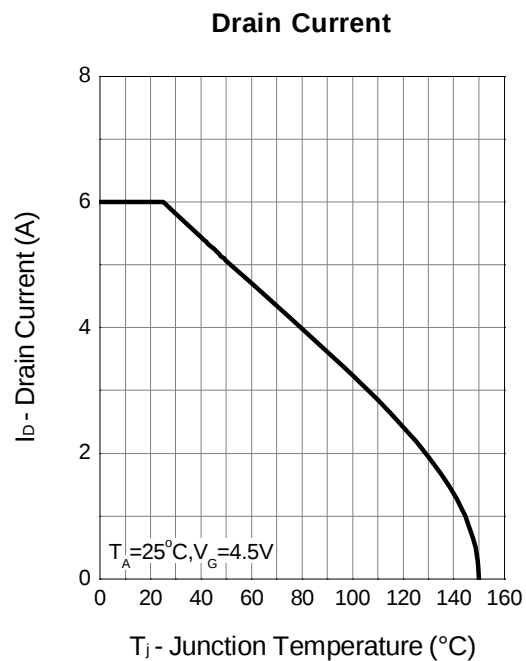
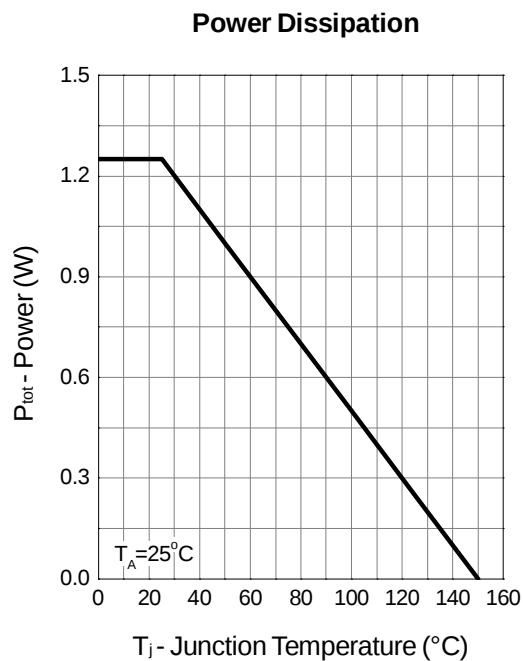
Symbol	Parameter	Test Condition	APM9988CO			Unit
			Min.	Typ.	Max.	
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz		2		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz		1155		pF
C _{oss}	Output Capacitance			200		
C _{rss}	Reverse Transfer Capacitance			90		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =10V, R _L =10Ω, I _{DS} =1A, V _{GEN} =4.5V, R _G =6Ω		7	14	ns
T _r	Turn-on Rise Time			10	19	
t _{d(OFF)}	Turn-off Delay Time			47	86	
T _f	Turn-off Fall Time			24	45	
t _{rr}	Reverse Recovery Time	I _{SD} =6A, dI _{SD} /dt=100A/μs		25		ns
Q _{rr}	Reverse Recovery Charge			9		nC

Notes:

a : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

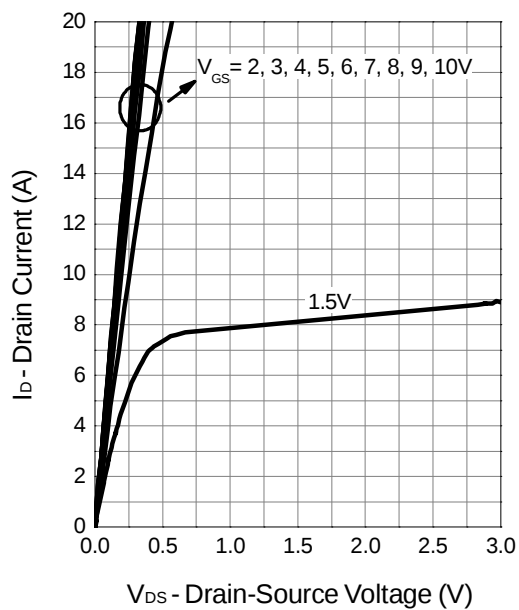
b : Guaranteed by design, not subject to production testing.

Typical Characteristics

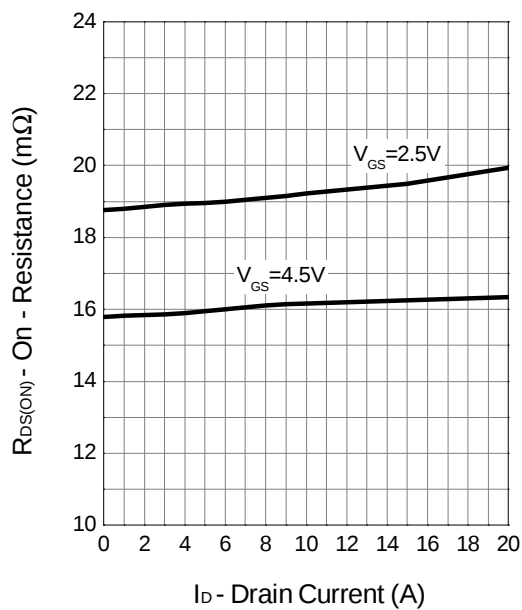


Typical Characteristics (Cont.)

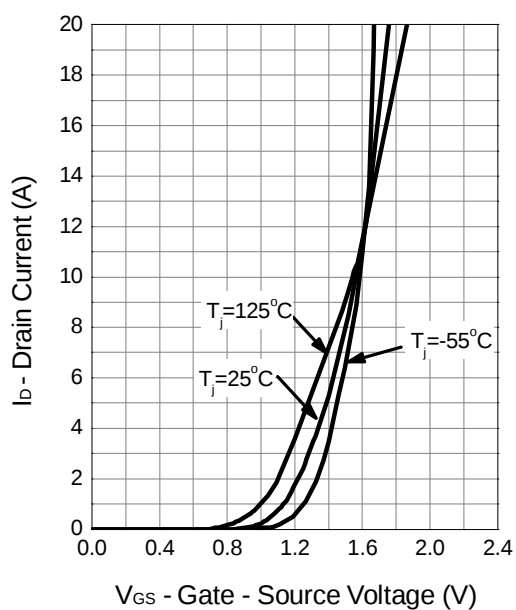
Output Characteristics



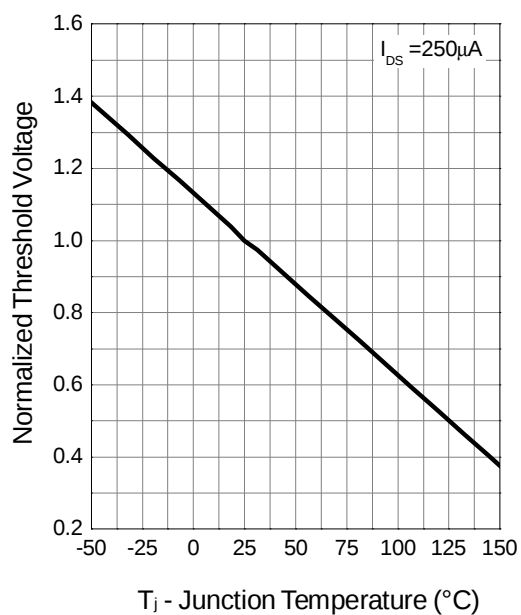
Drain-Source On Resistance



Transfer Characteristics

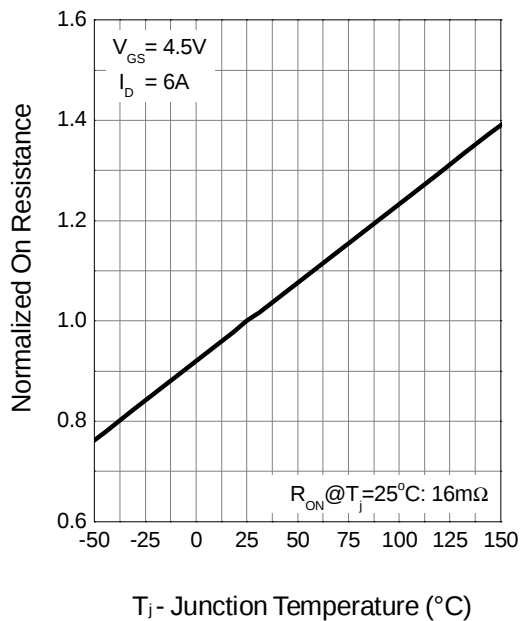


Gate Threshold Voltage

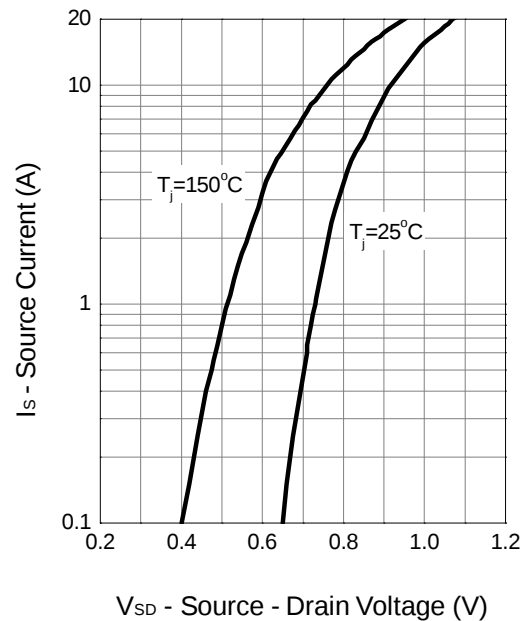


Typical Characteristics (Cont.)

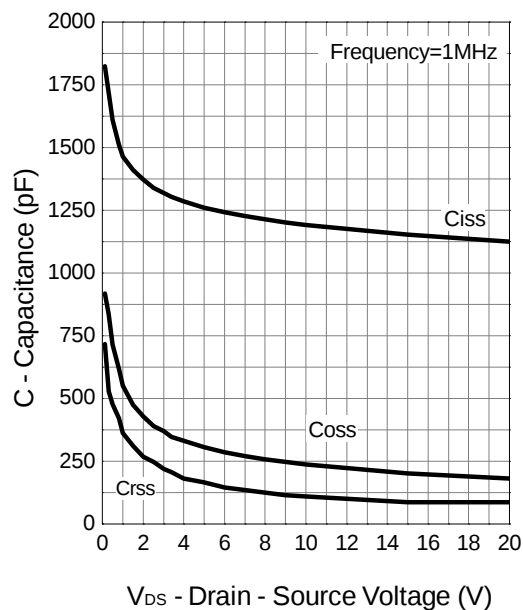
Drain-Source On Resistance



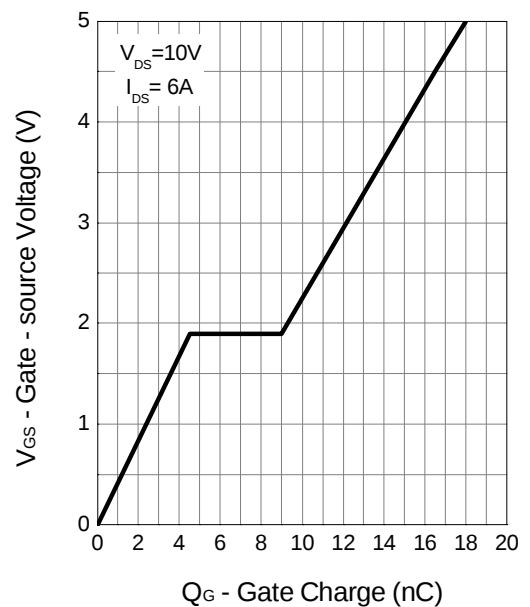
Source-Drain Diode Forward



Capacitance



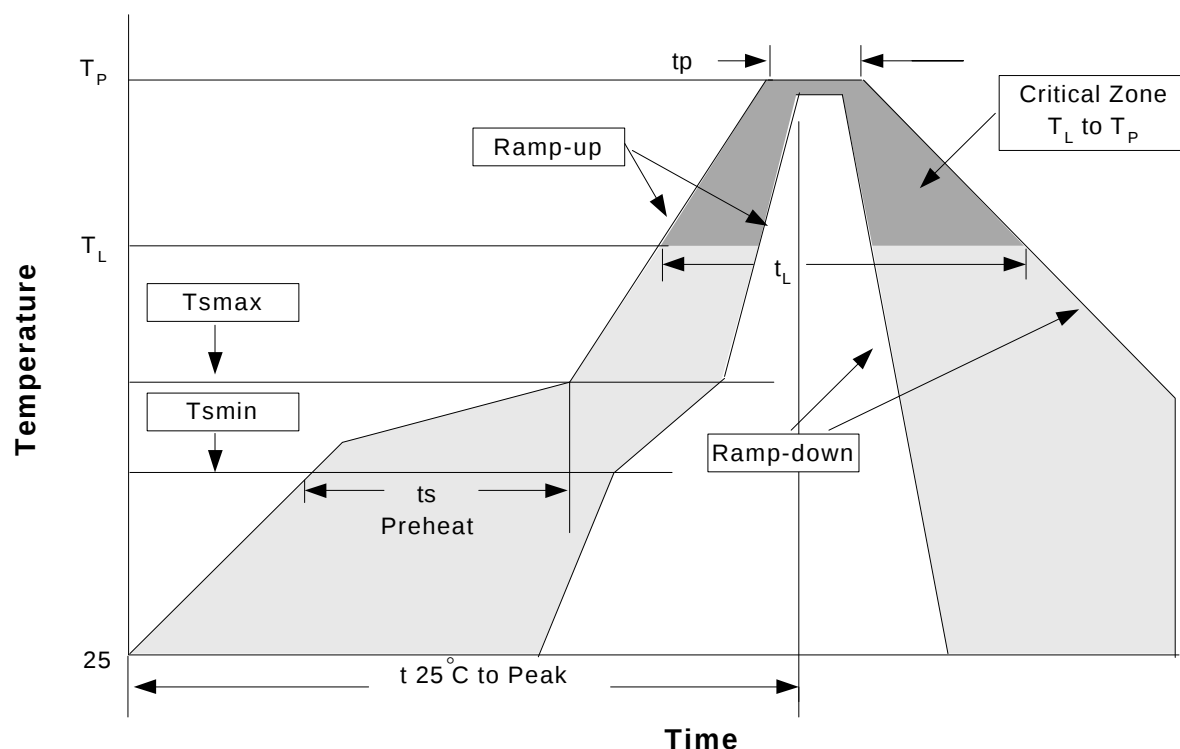
Gate Charge



Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.	3°C/second max.
Preheat - Temperature Min (T_{smin}) - Temperature Max (T_{smax}) - Time (min to max) (t_s)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: - Temperature (T_L) - Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak/Classification Temperature (T_P)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (t_p)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Notes: All temperatures refer to topside of the package .Measured on the body surface.

Classification Reflow Profiles(Cont.)

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

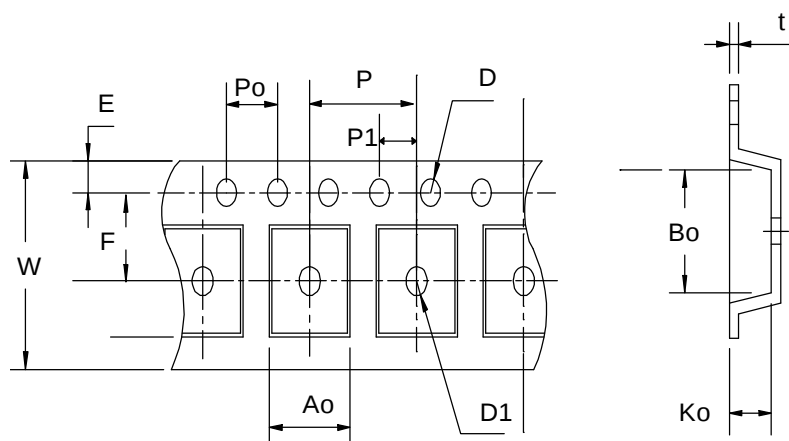
Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

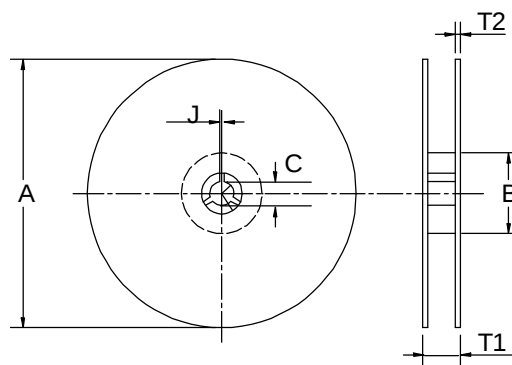
Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Carrier Tape & Reel Dimensions



Carrier Tape & Reel Dimensions(Cont.)



Application	A	B	C	J	T1	T2	W	P	E
TSSOP-8	330 ± 1	$62 +1.5$	$12.75 +0.15$	$2 + 0.5$	12.4 ± 0.2	2 ± 0.2	12 ± 0.3	8 ± 0.1	1.75 ± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	5.5 ± 0.1	1.5 ± 0.1	1.5 ± 0.1	4.0 ± 0.1	2.0 ± 0.1	7.0 ± 0.1	3.6 ± 0.3	1.6 ± 0.1	0.3 ± 0.013

(mm)

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
TSSOP- 8	12	9.3	2500

Customer Service

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